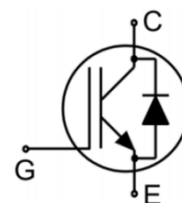


**Main Product Characteristics:**

|               |       |
|---------------|-------|
| $V_{CES}$     | 1250V |
| $I_C$         | 60A   |
| $V_{CE(sat)}$ | 1.7V  |


**TO - 247**

**Schematic Diagram**
**Features and Benefits:**

- Trench FS technology offering
- High speed switching
- Low gate charge and  $V_{CE(sat)}$
- High ruggedness, temperature stable behavior
- Maximum junction temperature 175°C


**Applications:**

- Solar Inverters
- Uninterruptible power supplies
- Motor drives
- Air condition

**Absolute Max Rating:**

| Symbol          | Parameter  | Value       | Units            |
|-----------------|--|-------------|------------------|
| $V_{CES}$       | Collector-Emitter Voltage  | 1250        | V                |
| $V_{GES}$       | Gate- Emitter Voltage  | $\pm 30$    | V                |
| $I_C$           | Collector Current  | 120         | A                |
|                 | Collector Current @ $T_c = 100\text{ }^\circ\text{C}$                  | 60          |                  |
| $I_{Cpuls}$     | Pulsed Collector Current, $t_p$ limited by $T_{jmax}$                  | 240         |                  |
| -               | Turn off safe operating area, $V_{CE}=1200V$ , $T_J=175^\circ\text{C}$ | 240         |                  |
|                 | Diode Continuous Forward Current @ $T_c = 100\text{ }^\circ\text{C}$   | 60          |                  |
| $I_{FM}$        | Diode Maximum Forward Current  | 240         |                  |
| $P_D$           | Power Dissipation @ $T_c = 25^\circ\text{C}$                           | 394         | W                |
| $T_J$ $T_{STG}$ | Operating Junction and Storage Temperature Range                       | -55 to +175 | $^\circ\text{C}$ |
| $T_L$           | Maximum Temperature for Soldering                                      | 260         | $^\circ\text{C}$ |

**Thermal Resistance**

| Symbol           | Characterizes                                  | Typ. | Max. | Units |
|------------------|--|------|------|-------|
| R <sub>θJC</sub> | Thermal Resistance, Junction-to-case for IGBT  | —    | 0.38 | °C/W  |
|                  | Thermal Resistance, Junction-to-case for Diode | —    | 0.69 | °C/W  |
| R <sub>θJA</sub> | Thermal Resistance, Junction-to-ambient        | —    | 40   | °C/W  |

**Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified**

| Symbol               | Parameter   | Min. | Typ. | Max. | Units | Conditions   |
|----------------------|---|------|------|------|-------|--|
| V <sub>(BR)CES</sub> | Collector-Emitter Breakdown Voltage                           | 1250 | —    | —    | V     | V <sub>GE</sub> =0V, I <sub>CE</sub> =1mA  |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage                          | —    | 1.7  | 2.0  | V     | I <sub>C</sub> =60A, V <sub>GE</sub> =15V<br>@T <sub>J</sub> =25°C                         |
| V <sub>GE(th)</sub>  | Gate Threshold Voltage  | 4.5  | —    | 6.5  | V     | I <sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>                                      |
| I <sub>CES</sub>     | Collector-Emitter Leakage Current                             | —    | —    | 1    | μA    | V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V  |
| I <sub>GES</sub>     | Gate to Emitter Reverse Leakage                               | —    | —    | 100  | nA    | V <sub>GE</sub> =30V, V <sub>CE</sub> =0V  |
|                      |   | —    | —    | -100 |       | V <sub>GE</sub> =-30V, V <sub>CE</sub> =0V   |
| C <sub>ies</sub>     | Input capacitance   | —    | 8086 | —    | pF    | V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 25V<br>f = 1MHz                                  |
| C <sub>oes</sub>     | Output capacitance  | —    | 241  | —    |       |  |
| C <sub>res</sub>     | Reverse transfer capacitance                                  | —    | 161  | —    |       |  |
| t <sub>d(on)</sub>   | Turn-on delay time  | —    | 64   | —    | ns    | V <sub>CC</sub> =600V, I <sub>C</sub> =60A,<br>V <sub>GE</sub> =0/15V, R <sub>g</sub> =10Ω |
| t <sub>r</sub>       | Rise time   | —    | 33   | —    |       |  |
| t <sub>d(off)</sub>  | Turn-Off delay time   | —    | 579  | —    |       |  |
| t <sub>f</sub>       | Fall time   | —    | 54   | —    |       |  |
| E <sub>on</sub>      | Turn-On Switching Loss  | —    | 5.78 | —    | mJ    | V <sub>CC</sub> =600V, I <sub>C</sub> =60A,<br>V <sub>GE</sub> =0/15V, R <sub>g</sub> =10Ω |
| E <sub>off</sub>     | Turn-Off Switching Loss                                       | —    | 3.84 | —    |       |  |
| E <sub>ts</sub>      | Total Switching Loss  | —    | 9.62 | —    |       |  |
| Q <sub>g</sub>       | Total Gate Charge   | —    | 240  | —    | nC    | V <sub>CC</sub> =480V, I <sub>C</sub> =60A,<br>V <sub>GE</sub> =15V                        |
| Q <sub>ge</sub>      | Gate to Emitter Charge  | —    | 65   | —    |       |  |
| Q <sub>gc</sub>      | Gate to Collector Charge                                      | —    | 95   | —    |       |  |
| I <sub>C(SC)</sub>   | Short circuit collector current                               | —    | 620  | —    | A     | V <sub>GE</sub> =15V, V <sub>CC</sub> ≤600V,<br>t <sub>sc</sub> ≤10μs                      |
|                      | Max.1000 short circuits<br>Time between short circuits: ≥1.0s | —    |      |      |       |  |

**Electrical Characteristics of the Diode @T<sub>A</sub>=25°C unless otherwise specified**

| Symbol           | Parameter                           | Min. | Typ. | Max. | Units | Conditions  |
|------------------|-------------------------------------|------|------|------|-------|---|
| V <sub>FM</sub>  | Diode Forward Voltage               | —    | 2.44 | 3    | V     | I <sub>F</sub> =60A   |
| t <sub>rr</sub>  | Reverse Recovery Time               | —    | 138  | —    | ns    | T <sub>J</sub> = 25°C, I <sub>F</sub> =60A,<br>V <sub>GE</sub> =0/15V, V <sub>R</sub> =600V |
| Q <sub>rr</sub>  | Reverse Recovery Charge             | —    | 1.71 | —    | μC    |   |
| I <sub>RRM</sub> | Diode Peak Reverse Recovery Current | —    | 26.4 | —    | A     |   |

Typical Electrical and Thermal Characteristics

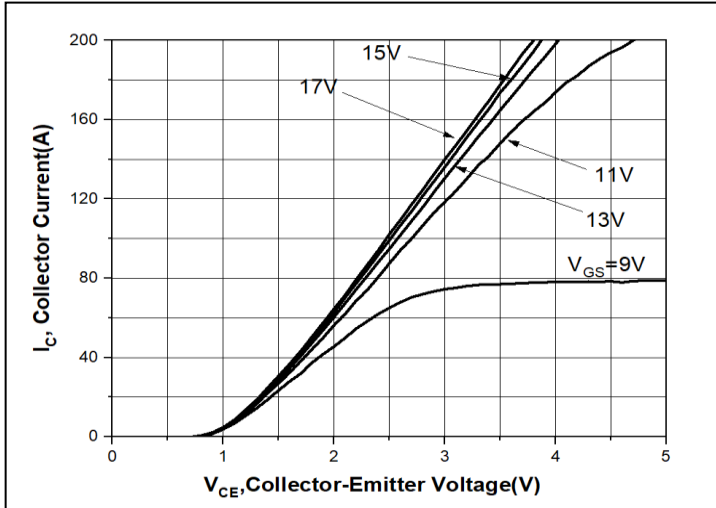


Figure1. Typical Output Characteristics

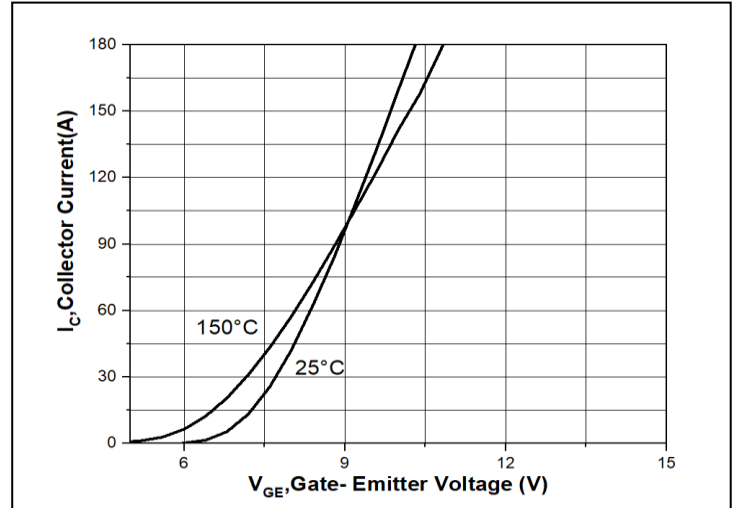


Figure2. Typical Transfer Characteristics

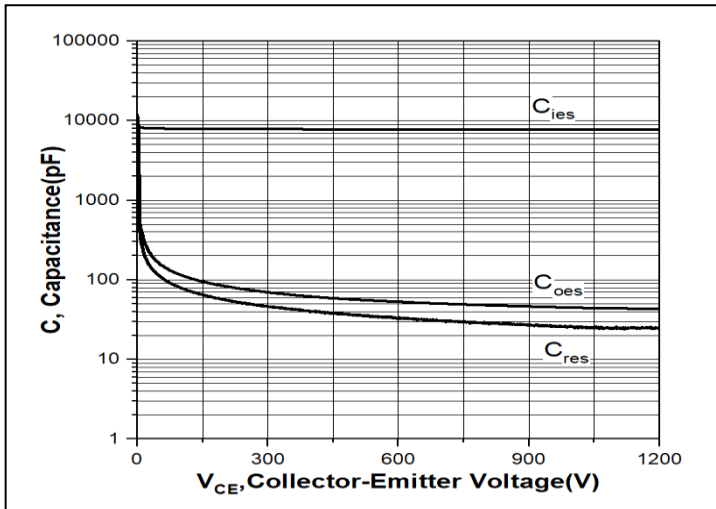


Figure3. Typical Capacitance

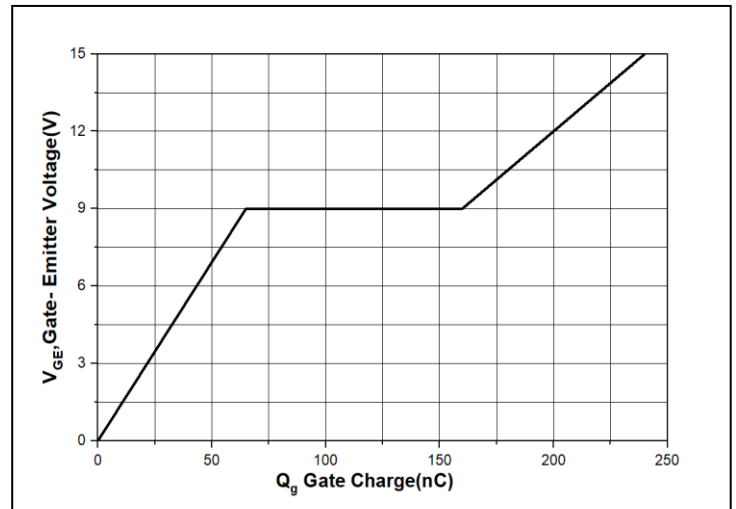


Figure4. Typical Gate Charge

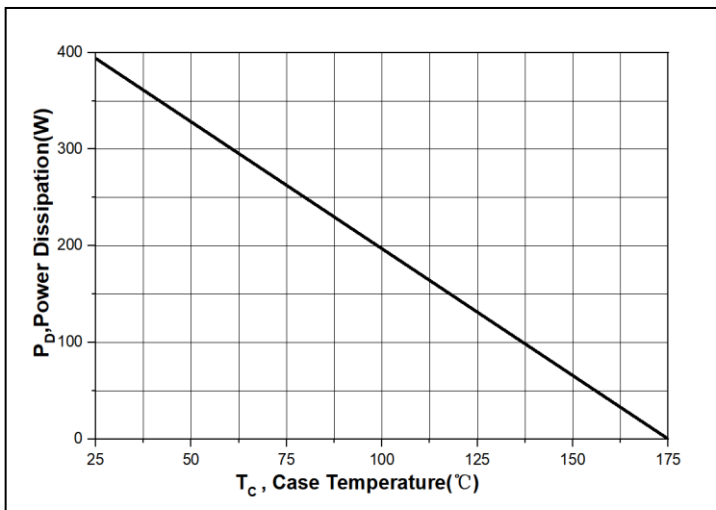


Figure5. Power Dissipation vs. Case Temperature

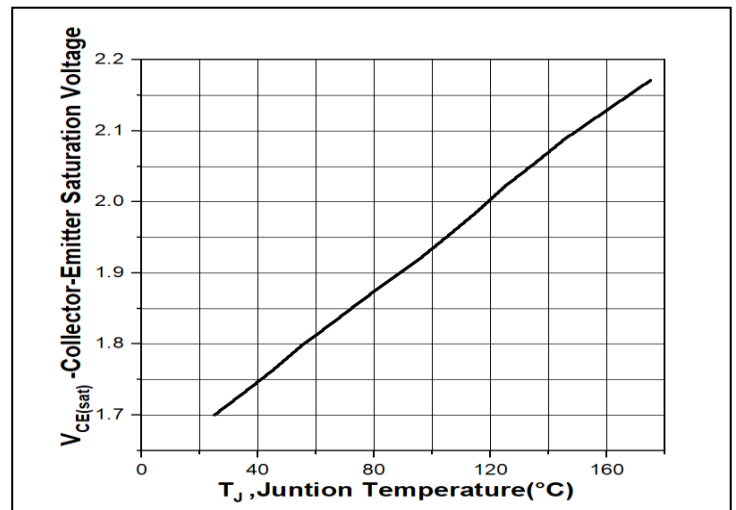


Figure6. Collector-Emitter Saturation Voltage vs. Temperature

Typical Electrical and Thermal Characteristics

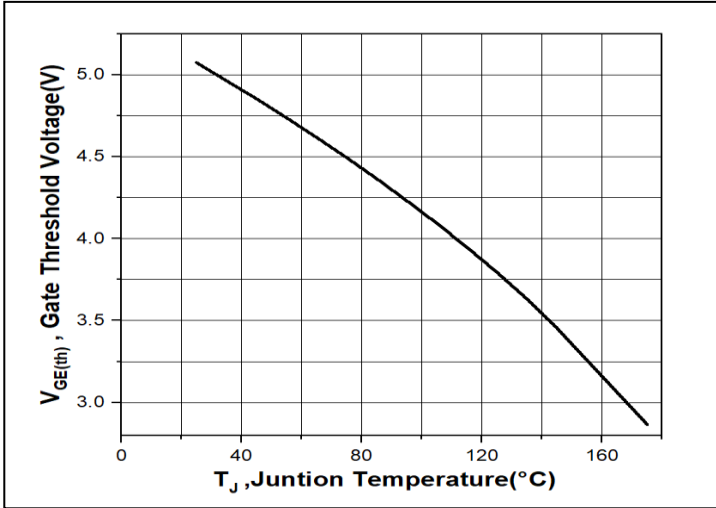


Figure7. Gate Threshold Voltage vs. Temperature

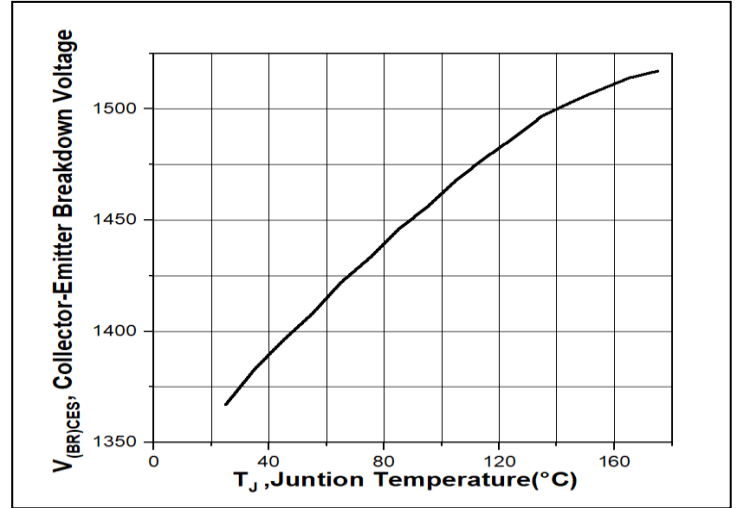


Figure8. Collector-Emitter Breakdown Voltage vs. Temperature

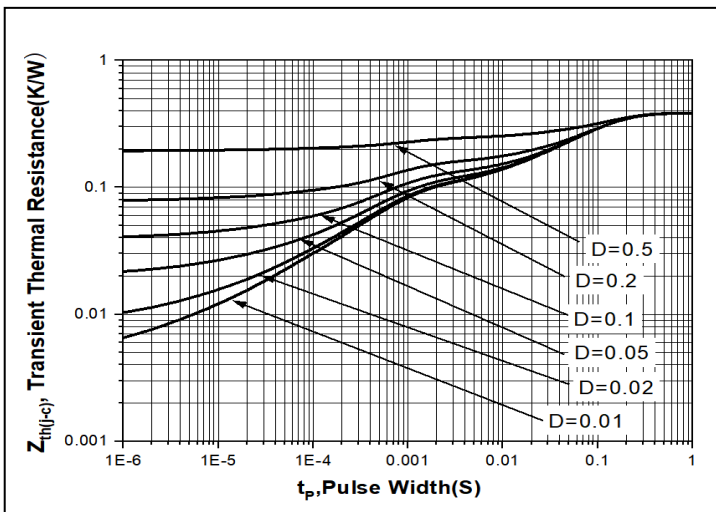


Figure9. IGBT transient thermal resistance ( $D = t_p/T$ )

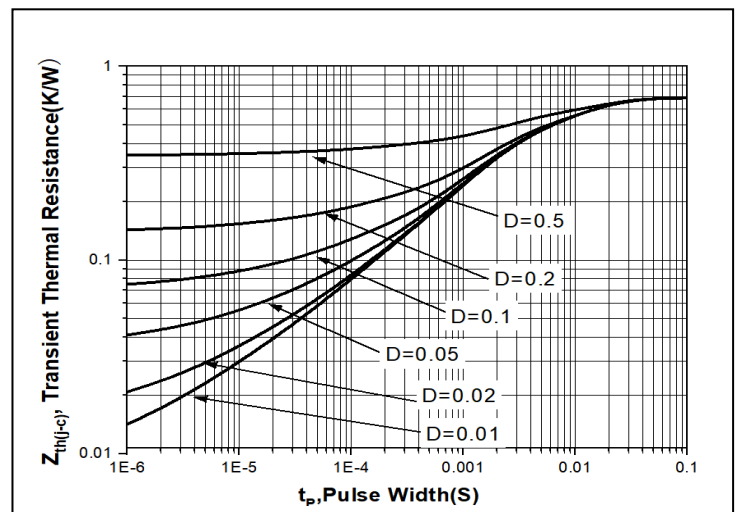
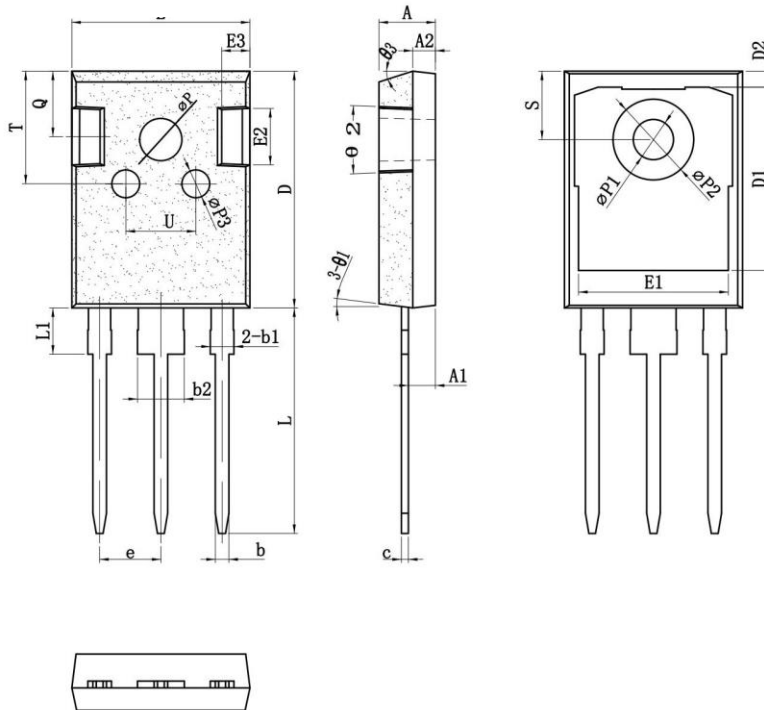
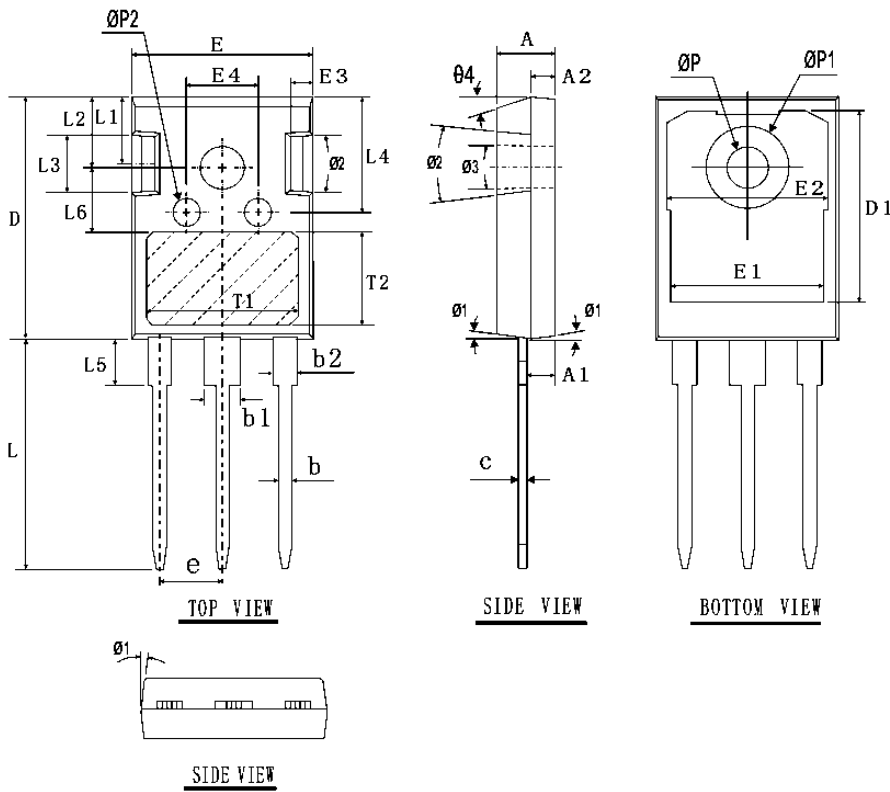


Figure10. Diode transient thermal impedance as a function of pulse width ( $D = t_p/T$ )

**Mechanical Data:**
**Option1:**
**Unit:mm**


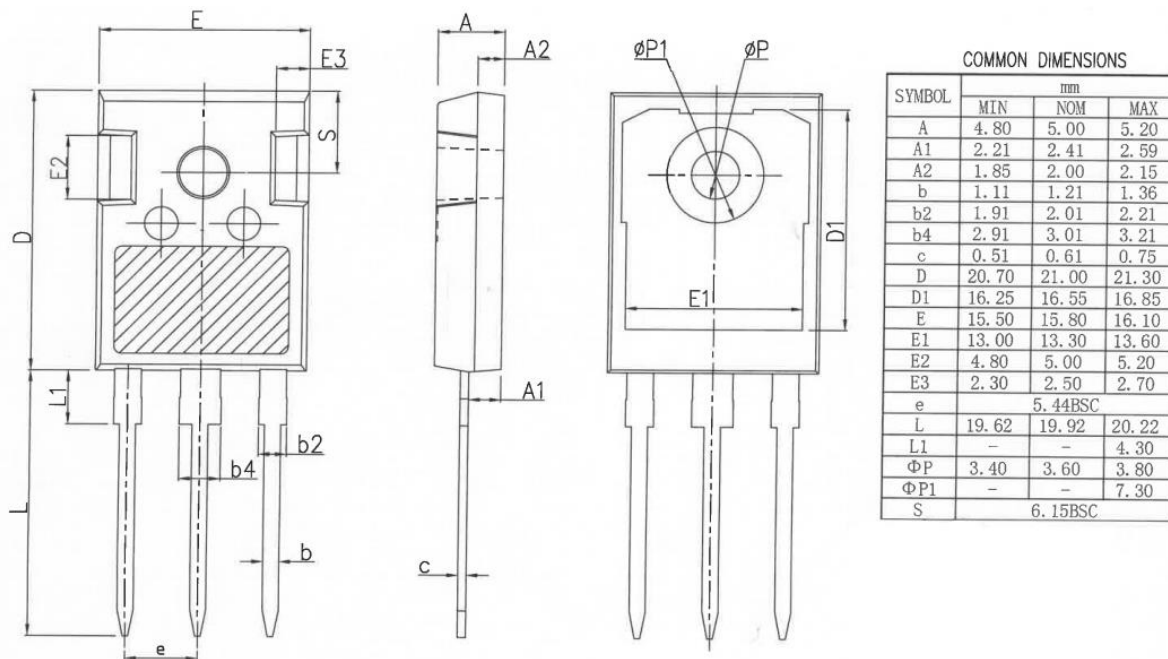
| SYMBOL | mm    |       |       |
|--------|-------|-------|-------|
|        | MIN   | NOM   | MAX   |
| *A     | 4.90  | 5.00  | 5.10  |
| *A1    | 2.31  | 2.41  | 2.51  |
| A2     | 1.90  | 2.00  | 2.10  |
| *b     | 1.15  | 1.20  | 1.25  |
| *b1    | 1.95  | 2.10  | 2.25  |
| *b2    | 2.95  | 3.10  | 3.25  |
| *c     | 0.55  | 0.60  | 0.65  |
| *D     | 20.90 | 21.00 | 21.10 |
| D1     | 16.35 | 16.55 | 16.75 |
| D2     | 1.05  | 1.20  | 1.35  |
| *E     | 15.70 | 15.80 | 15.90 |
| E1     | 13.10 | 13.25 | 13.40 |
| E2     | 4.90  | 5.00  | 5.10  |
| E3     | 2.40  | 2.50  | 2.60  |
| *e     | 5.40  | 5.44  | 5.48  |
| *L     | 19.80 | 19.98 | 20.15 |
| *L1    | -     | -     | 4.30  |
| *ΦP    | 3.60  | 3.70  | 3.80  |
| *ΦP1   | 3.45  | 3.55  | 3.65  |
| ΦP2    | 7.03  | 7.18  | 7.33  |
| ΦP3    | 2.40  | 2.50  | 2.60  |
| Q      | 5.60  | 5.80  | 6.00  |
| *S     | 6.05  | 6.15  | 6.25  |
| T      | 9.80  | 10.00 | 10.20 |
| U      | 6.00  | 6.20  | 6.40  |
| θ1     | 5°    | 7°    | 9°    |
| θ2     | 1°    | 3°    | 5°    |
| θ3     | 13°   | 15°   | 17°   |

## Option2:



COMMON DIMENSIONS  
(UNITS OF MEASURE=mm)

| SYMBOL | MIN      | NOM   | MAX   |
|--------|----------|-------|-------|
| A      | 4.80     | 5.00  | 5.20  |
| A1     | 2.20     | 2.40  | 2.60  |
| A2     | 1.85     | 2.00  | 2.15  |
| b      | 1.10     | 1.20  | 1.30  |
| b1     | 2.80     | 3.00  | 3.20  |
| b2     | 1.80     | 2.00  | 2.20  |
| C      | 0.52     | 0.62  | 0.72  |
| D      | 20.35    | 20.65 | 20.95 |
| D1     | 16.35    | 16.55 | 16.75 |
| E      | 15.50    | 15.80 | 16.10 |
| E1     | 13.10    | 13.30 | 13.50 |
| E2     | 13.80    | 14.00 | 14.20 |
| E3     | 1.45     | 1.60  | 1.75  |
| E4     | 6.00     | 6.20  | 6.40  |
| L      | 19.80    | 20.00 | 20.20 |
| L1     | 5.88     | 5.98  | 6.08  |
| L2     | 5.88     | 5.98  | 6.08  |
| L3     | 4.90     | 5.00  | 5.10  |
| L4     | 9.70     | 9.80  | 9.90  |
| L5     | 4.10     | 4.30  | 4.50  |
| Ø1     | 4°       | 7°    | 10°   |
| Ø2     | 11°      | 14°   | 17°   |
| Ø3     | 1°       | —     | 2°    |
| Ø4     | 10°      | 15°   | 20°   |
| ØP     | 3.35     | 3.60  | 3.85  |
| ØP1    | —        | —     | 7.30  |
| ØP2    | 2.25     | 2.50  | 2.75  |
| e      | 5.44BSC  |       |       |
| T1     | 12.80REF |       |       |
| T2     | 7.80REF  |       |       |
| L6     | 5.50REF  |       |       |

**Option3:**


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